



S8550LT1

PNP EPITAXIAL SILICON TRANSISTORS

HIGH VOLTAGE TRANSISTOR: (PNP)

FEATURES

Die Size

0.44*0.44mm

Power dissipation

$P_{CM} : 225mW (T_{amb}=25^{\circ}C)$

Collector current

$I_{CM} : 0.5A$

Collector-base voltage

$V_{(BR)CBO} : 40V$

SOT-23



1. BASE

2. EMITTER

3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	21			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5.0			V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			100	nA
DC current gain	$H_{FE(1)}$	$V_{CE}=1V, I_C=150mA$	120		400	
	$H_{FE(2)}$	$V_{CE}=1V, I_C=500mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			500	mV
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$			1.2	V
Base-emitter voltage	$V_{BE(on)}$	$I_C=10mA, V_{CE}=1V$			1.0	V

CLASSIFICATION OF $H_{FE(1)}$

Rank	B9C	B9D	B9E
Range	120-200	160-300	280-400